

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
80V	9mΩ@10V	60A
	12mΩ@4.5V	



合肥矽普半导体

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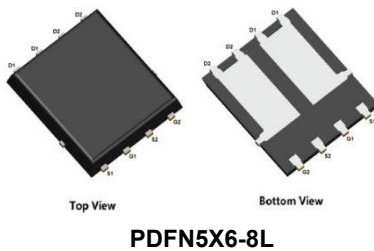
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

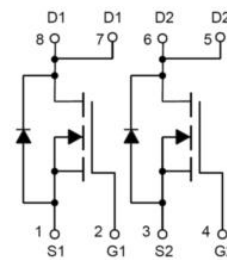
Applications

- Power switching application
- DC-DC Converter
- Uninterruptible power supply

Package



Circuit diagram



Marking



SP80N09GDNK :Device Code
** :Week Code

Order Information

Device	Package	Unit/Tape
SP80N09GDNK	PDFN5X6-8L	5000

Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	80	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Tc=25°C)	I_D	60	A
Continuous Drain Current (Tc=100°C)	I_D	38	A
Pulse Drain Current Tested	I_{DM}	240	A
Single Pulse Avalanche Energy ¹	E_{AS}	156	mJ
Power Dissipation (Tc=25°C)	P_D	71.4	W
Power Dissipation (Tc=100°C)	P_D	23.8	W
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	1.75	°C/W
Maximum Junction Temperature	T_J	-55 to 150	°C
Storage Temperature Range	T_{STG}	-55 to 150	°C

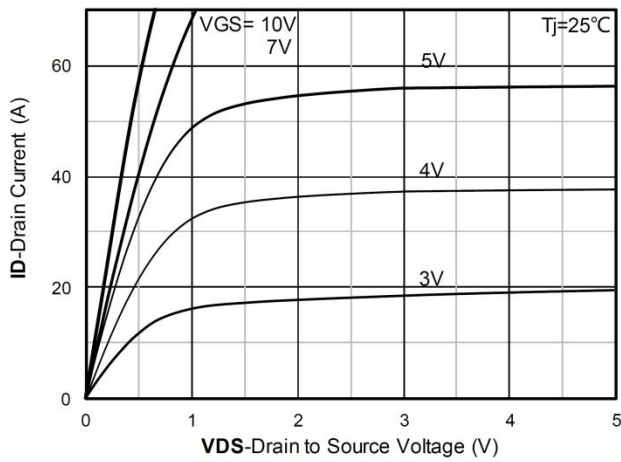
Electrical characteristics (Ta=25°C, unless otherwise noted)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	ID = 250μA, VGS = 0V	80	-	-	V
Zero Gate Voltage Drain Current	IDSS	VDS = 64V, VGS = 0V	-	-	1	uA
Gate Leakage Current	IGSS	VGS = ±20V, VDS = 0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	VDS = VGS, ID = 250μA	1.4	1.8	2.4	V
Drain-Source On-state Resistance	RDS(ON)	VGS = 10V, ID = 20A	-	9	13.5	mΩ
		VGS = 4.5V, ID = 20A	-	12	18	
Gate Resistance	RG	VDS=40V , VGS=0V , f=1MHz	-	1.8	-	Ω
Dynamic Characteristics						
Input Capacitance	Ciss	VGS = 0V, VDS = 40V, F = 1MHz	-	1232	-	pF
Output Capacitance	Coss		-	357	-	
Reverse Transfer Capacitance	Crss		-	16	-	
Total Gate Charge	Qg	VDS = 40V, VGS = 10V, ID = 20A	-	20	-	nC
Gate-Source Charge	Qgs		-	5.9	-	
Gate-Drain Charge	Qgd		-	5.4	-	
Gate Plateau Voltage	Vplateau		-	3.4	-	V
Switching Characteristics						
Turn-On Delay Time	td(on)	VDD = 40V, ID = 20A, VGS = 10V, RG = 3Ω	-	9.8	-	nS
Rise Time	tr		-	6.9	-	
Turn-Off Delay Time	td(off)		-	17	-	
Fall Time	tf		-	5.9	-	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	VSD	VGS = 0V, IS = 1A, TJ = 25℃	-	-	1.2	V
Maximum Body-Diode Continuous Current	IS		-	-	60	A
Reverse Recovery Time	Trr	IS = 20A, di/dt = 100A/μs, TJ = 25℃	-	43	-	nS
Reverse Recovery Charge	Qrr		-	34.2	-	nC

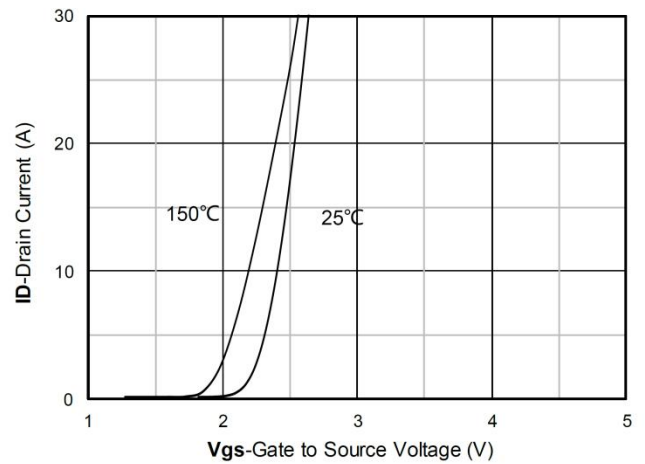
Note :

1. The test condition is $V_{DD} = 40V, V_{GS} = 10V, L = 0.5mH, R_G = 25\Omega$

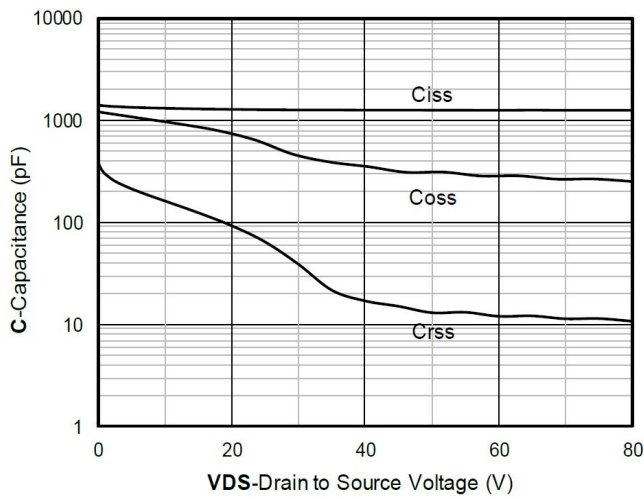
Typical Characteristics



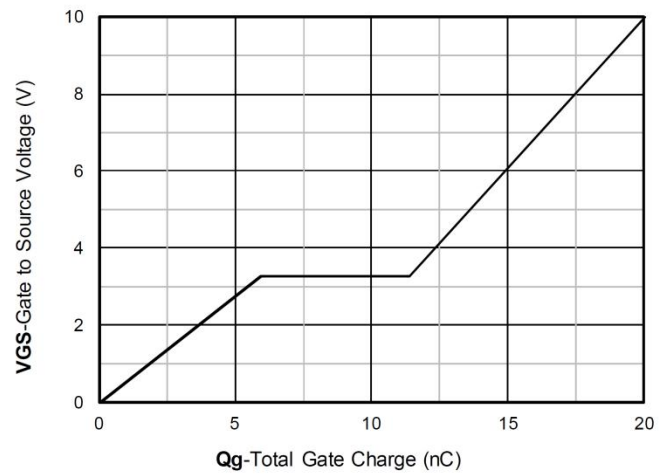
Output Characteristics



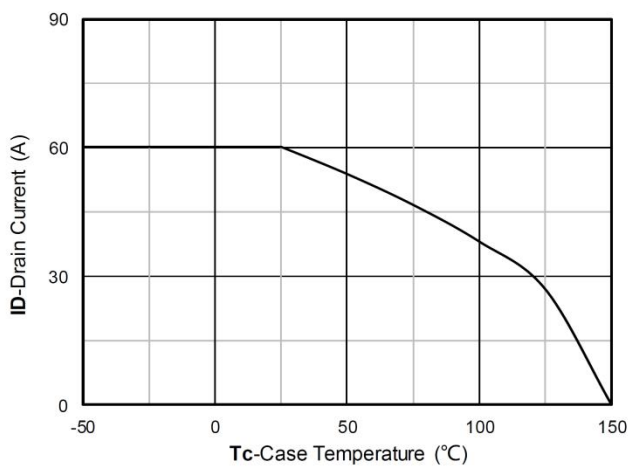
Transfer Characteristics



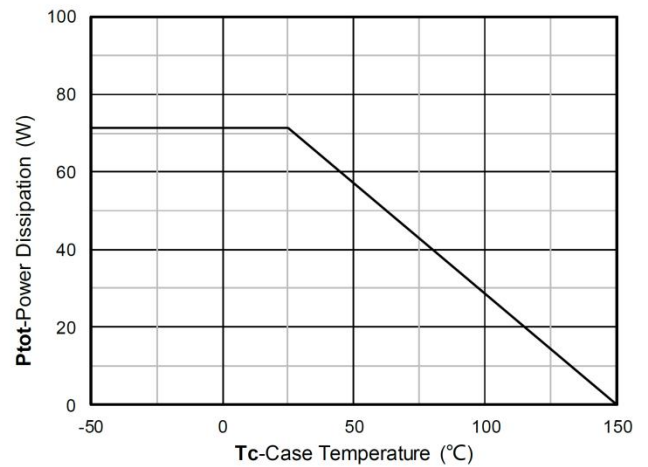
Capacitance Characteristics



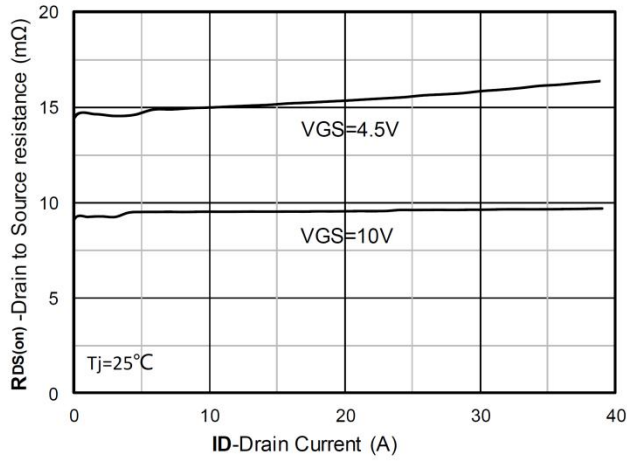
Gate Charge



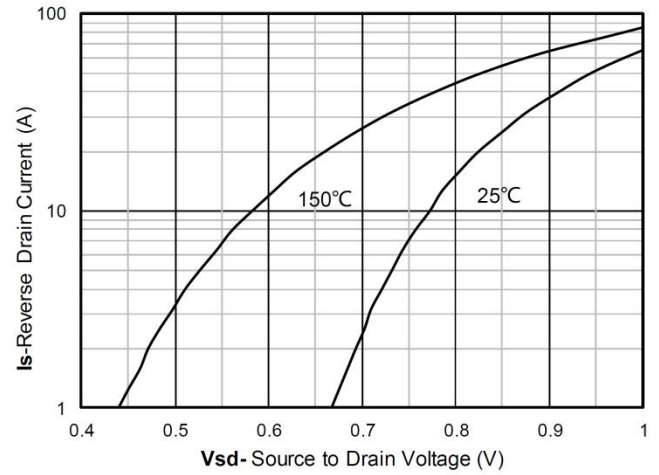
Current dissipation



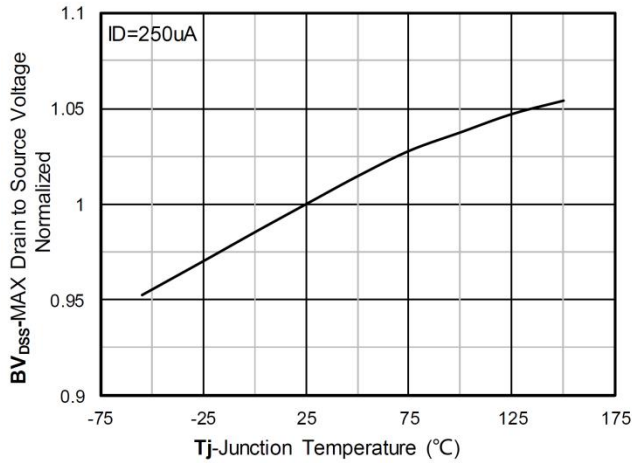
Power dissipation



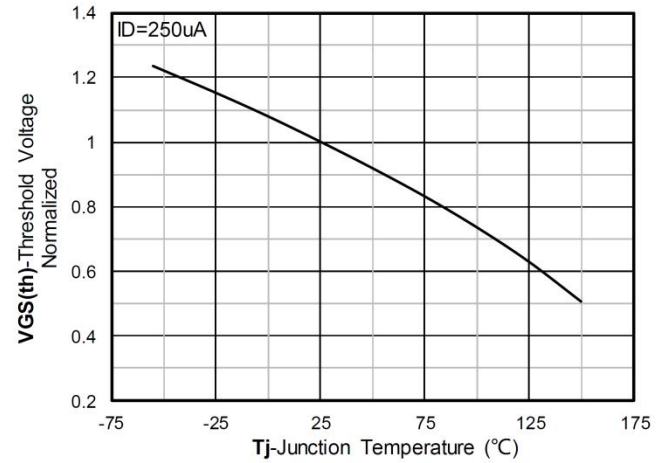
RDS(on) VS Drain Current



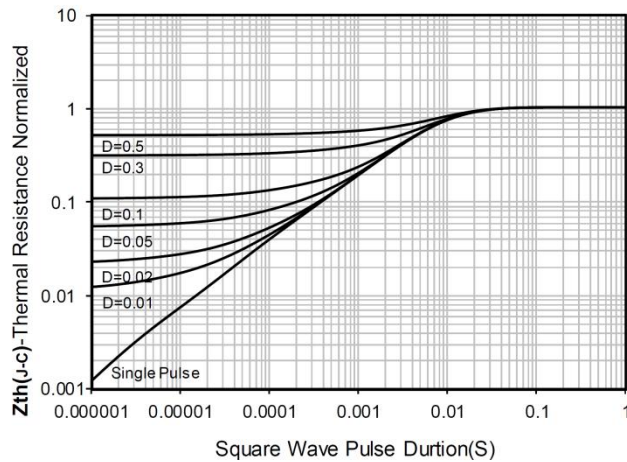
Forward characteristics of reverse diode



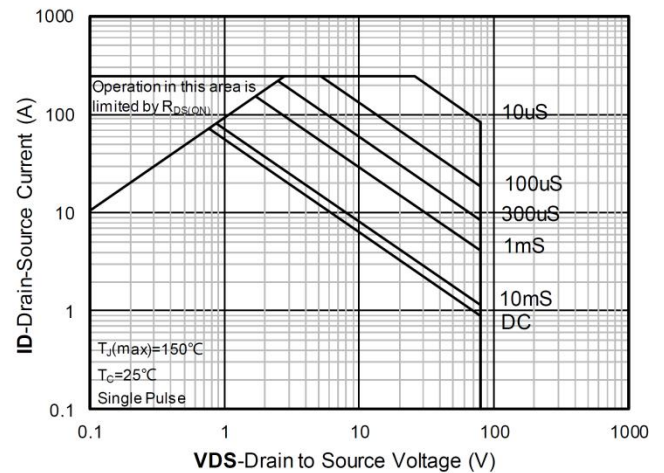
Normalized breakdown voltage



Normalized Threshold voltage



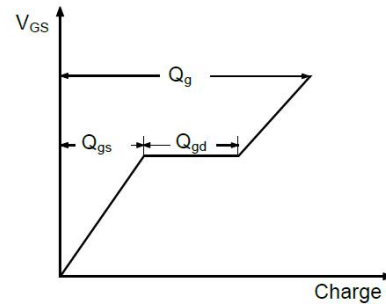
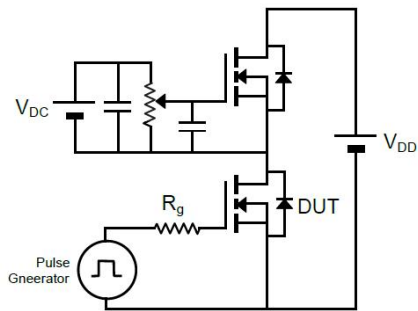
Normalized Maximum Transient Thermal Impedance



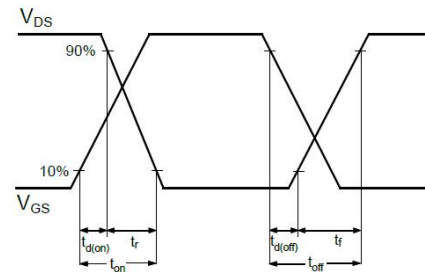
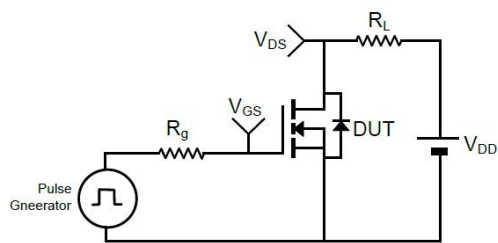
Safe Operation Area

Test Circuit

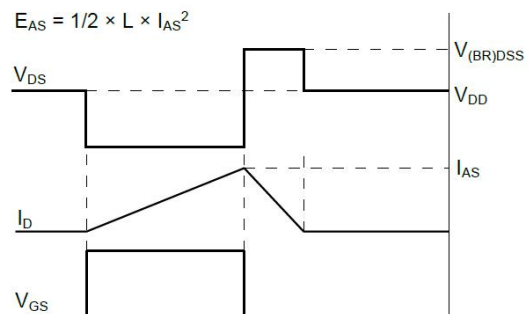
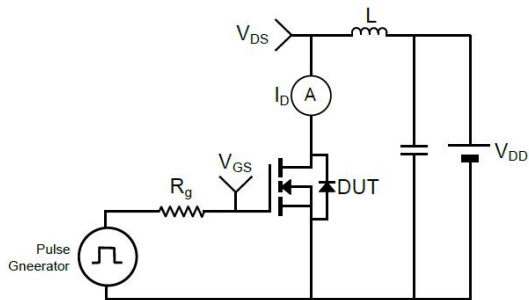
Gate Charge



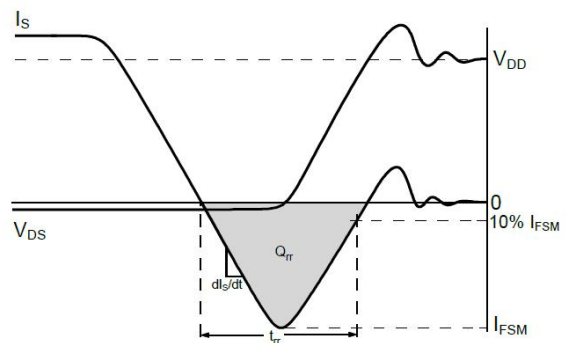
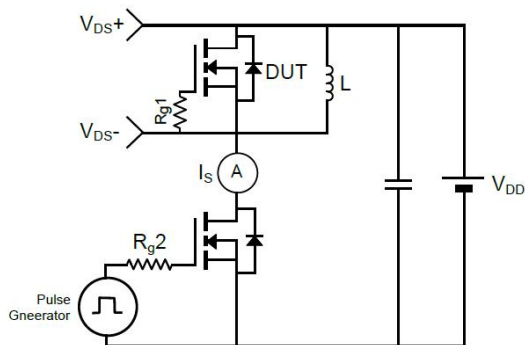
Resistive Load Switching Time



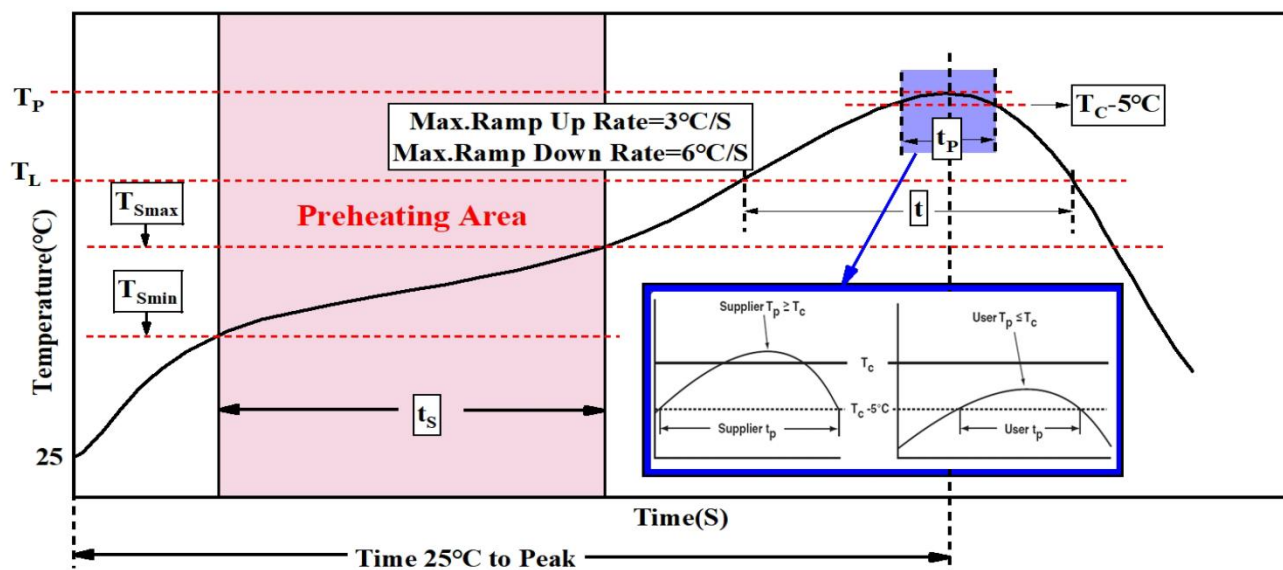
Un-clamped Inductive Load Switching



Drain-Source Body Diode Reverse Recovery



Temperature Profile for IR Reflow Soldering



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T _{min})	100°C	150°C
Temperature max (T _{max})	150°C	200°C
Time (T _{min} to T _{max}) (t _s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T _{max} to T _p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T _L)	183 °C	217°C
Time at liquidous (t _L)	60-150 seconds	60-150 seconds
Peak package body Temperature e (T _p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t _p)** within 5°C of the specified classification temperature (T _c)	20** seconds	30** seconds
Average ramp-down rate (T _p to T _{max})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T _p) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t _p) is defined as a supplier minimum and a user maximum		

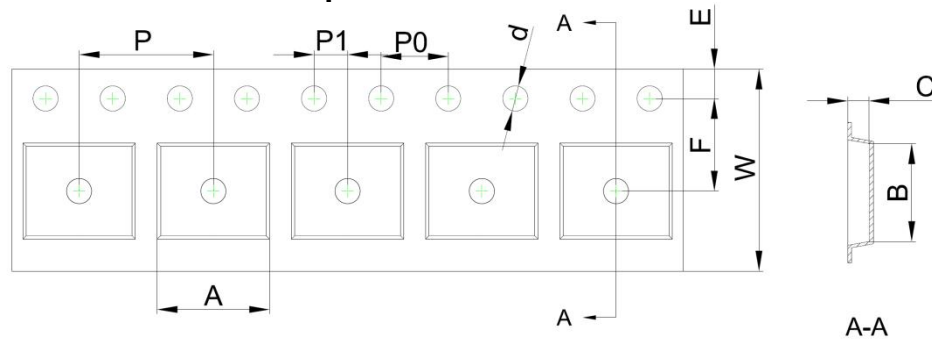
Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

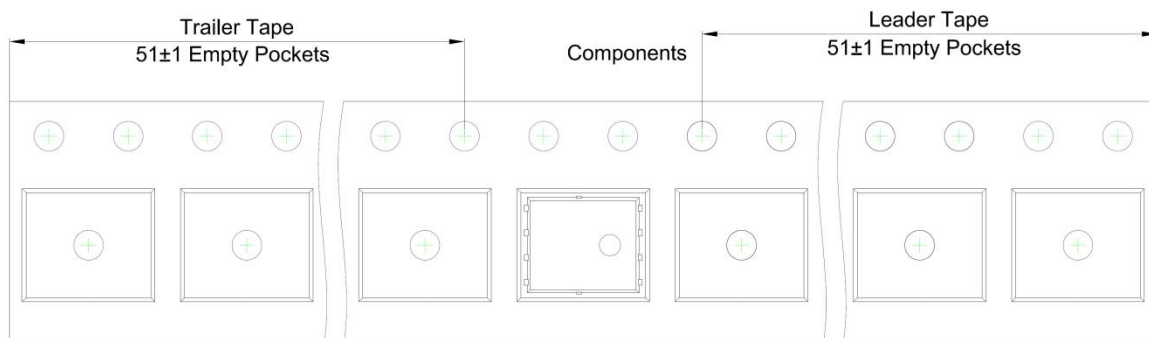
PDFN5X6-8L Embossed Carrier Tape



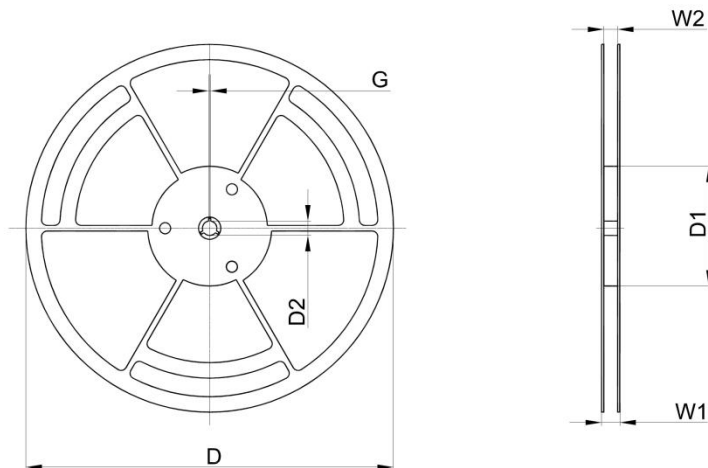
Dimensions are in millimeter

Pkg type	A	B	C	d	E	F	P0	P	P1	W
PDFN5X6-8L	6.30	5.30	1.10	Φ1.50	1.75	5.50	4.00	8.00	2.00	12.00

PDFN5X6-8L Tape Leader and Trailer



PDFN5X6-8L Reel

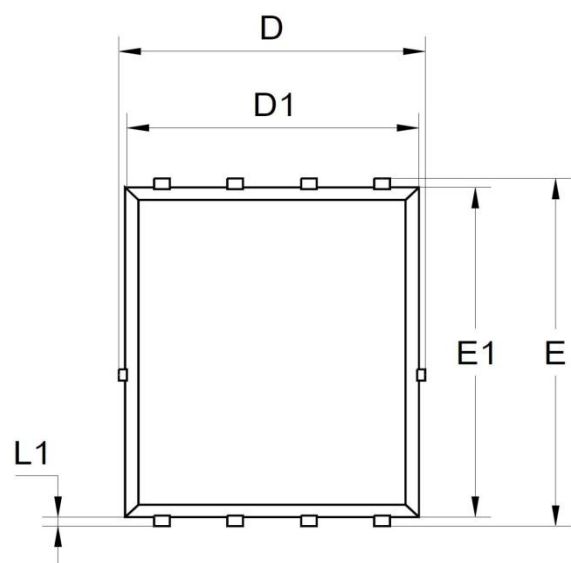


Dimensions are in millimeter

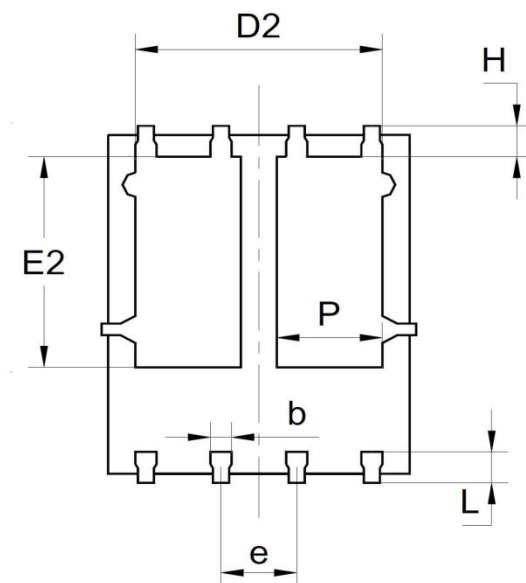
Reel Option	D	D1	D2	G	W1	W2
13"Dia	Ø330.00	100.00	13.00	1.90	17.60	12.40

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)
5,000 pcs	13 inch	5,000 pcs	340×336×29	50,000 pcs	353×346×365

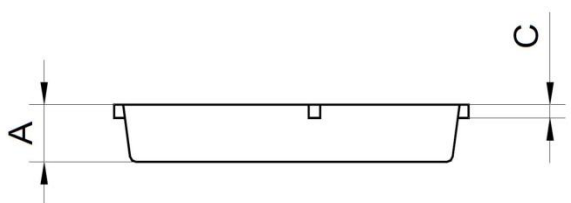
PDFN5X6-8L Package Information



Top View
[顶视图]



Bottom View
[背视图]



Side View
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.120	0.035	0.044
b	0.330	0.510	0.013	0.020
C	0.110	0.340	0.004	0.013
D	4.700	5.260	0.185	0.207
D1	4.700	5.100	0.185	0.201
D2	3.560	4.500	0.140	0.177
E	5.750	6.250	0.226	0.246
E1	5.600	6.000	0.220	0.236
E2	3.180	3.660	0.125	0.144
e	1.170	1.370	0.046	0.054
L	0.350	0.710	0.014	0.028
L1	0.060	0.200	0.002	0.008
H	0.350	0.710	0.014	0.028
P	1.700	2.300	0.067	0.091